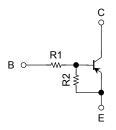
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

RN2961FS,RN2962FS,RN2963FS, RN2964FS,RN2965FS,RN2966FS

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Two devices are incorporated into a fine pitch Small Mold (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.
 Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN1961FS~RN1966FS

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2961FS	4.7	4.7
RINZ901F3	4.7	4.7
RN2962FS	10	10
RN2963FS	22	22
RN2964FS	47	47
RN2965FS	2.2	47
RN2966FS	4.7	47

1.0±0.05 0.1±0.05 0.8±0.05 0.1±0.05 0.15±0.05 6 5 .0±0.05 0.7 ± 0.05 0.1 ± 0.05 1.EMIITTER1 (E1) (E2) 2.EMITTER2 (B2) 3.BASE2 4.COLLECTOR2 (C2) 5.BASE1 fS6 6.COLLECTOR1

Unit: mm

Weight: 0.001g (typ.)

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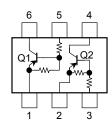
Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN2961FS~2966FS	V_{CBO}	-20	V	
Collector-emitter voltage	10129011 3 · 29001 3	V_{CEO}	-20	V	
Emitter-base voltage	RN2961FS~2964FS	V _{EBO}	-10	V	
	RN2965FS, 2966FS	VEBO	-5		
Collector current		IC	-50	mA	
Collector power dissipation	RN2961FS~2966FS	P _C (Note)	50	mW	
Junction temperature	KN2901F3~2900F3	Tj	150	°C	
Storage temperature range		T _{stg}	−55~150	°C	

Note: Total rating

Equivalent Circuit (top view)

2-1F1C

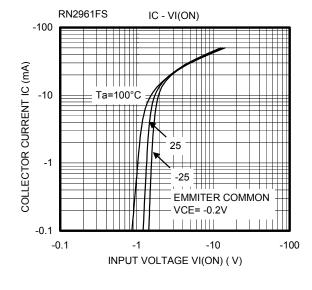


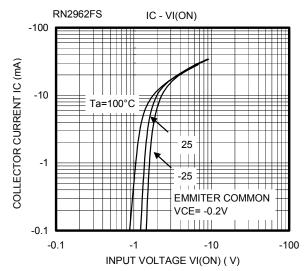


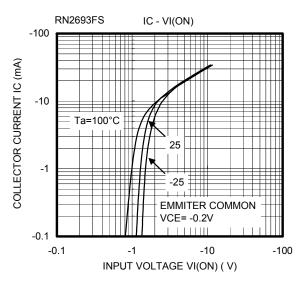
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

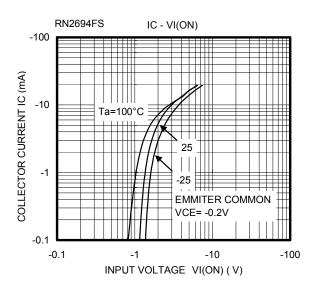
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2961FS~2966FS	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$	_	_	-100	nA
		I _{CEO}	$V_{CE} = -20 \text{ V}, I_B = 0$	_	_	-500	
Emitter cut-off current	RN2961FS	ІЕВО	$V_{EB} = -10 \text{ V}, I_{C} = 0$	-0.89	_	-1.33	- mA
	RN2962FS			-0.41	_	-0.63	
	RN2963FS			-0.18	_	-0.29	
	RN2964FS			-0.088	_	-0.133	
	RN2965FS		$V_{EB} = -5 \text{ V}, I_{C} = 0$	-0.085	_	-0.127	
	RN2966FS		vEB = −3 v, iC = 0	-0.08	_	-0.121	
	RN2961FS		$V_{CE} = -5 \text{ V},$ $I_{C} = -10 \text{ mA}$	30	_	_	
	RN2962FS			60	_	_	
DC ourrent gain	RN2963FS] _h		100	_	_	
DC current gain	RN2964FS	- h _{FE}		120	_	_	
	RN2965FS			120	_	_	
	RN2966FS			120	_	_	
Collector-emitter saturation voltage	RN2961FS~2966FS	V _{CE (sat)}	$I_C = -5 \text{ mA},$ $I_B = -0.25 \text{ mA}$	_	_	-0.15	٧
	RN2961FS		$V_{CE} = -0.2 \text{ V},$ $I_{C} = -5 \text{ mA}$	-1.0	_	-2.0	V
	RN2962FS	VI (ON)		-1.0	_	-2.2	
	RN2963FS			-1.1	_	-2.7	
Input voltage (ON)	RN2964FS			-1.2	_	-3.6	
	RN2965FS			-0.6	_	-1.1	
	RN2966FS			-0.6	_	-1.2	
Input voltage (OFF)	RN2961FS~2964FS	V _{I (OFF)}	$V_{CE} = -5 \text{ V},$ $I_{C} = -0.1 \text{ mA}$	-0.8	_	-1.5	V
	RN2965FS, 2966FS			-0.4	_	-0.8	
Collector output capacitance	RN2961FS~2966FS	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz	_	1.2	_	pF
Input resistor	RN2961FS	- R1	_	3.76	4.7	5.64	kΩ
	RN2962FS			8	10	12	
	RN2963FS			17.6	22	26.4	
	RN2964FS			37.6	47	56.4	
	RN2965FS			1.76	2.2	2.64	
	RN2966FS			3.76	4.7	5.64	
Resistor ratio	RN2961FS~2964FS	R1/R2	_	8.0	1.0	1.2	
	RN2965FS			0.0376	0.0468	0.0562	
	RN2966FS			0.08	0.1	0.12	

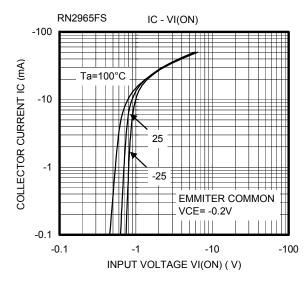
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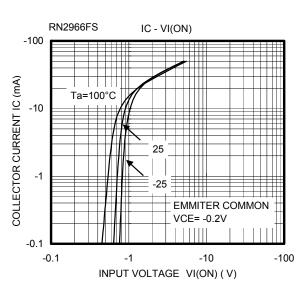


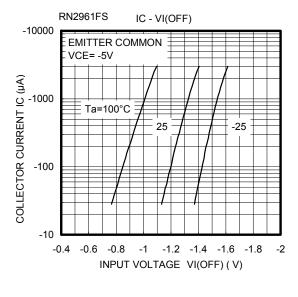


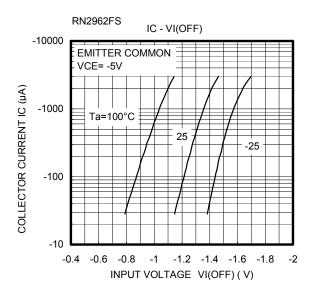


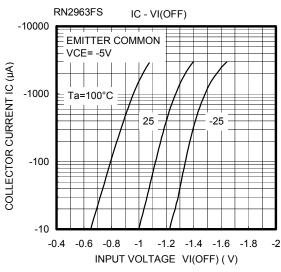


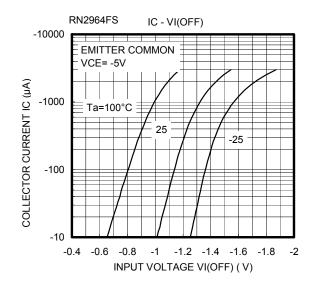


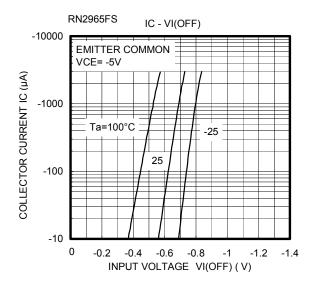


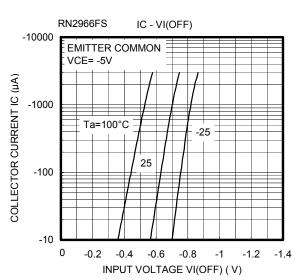


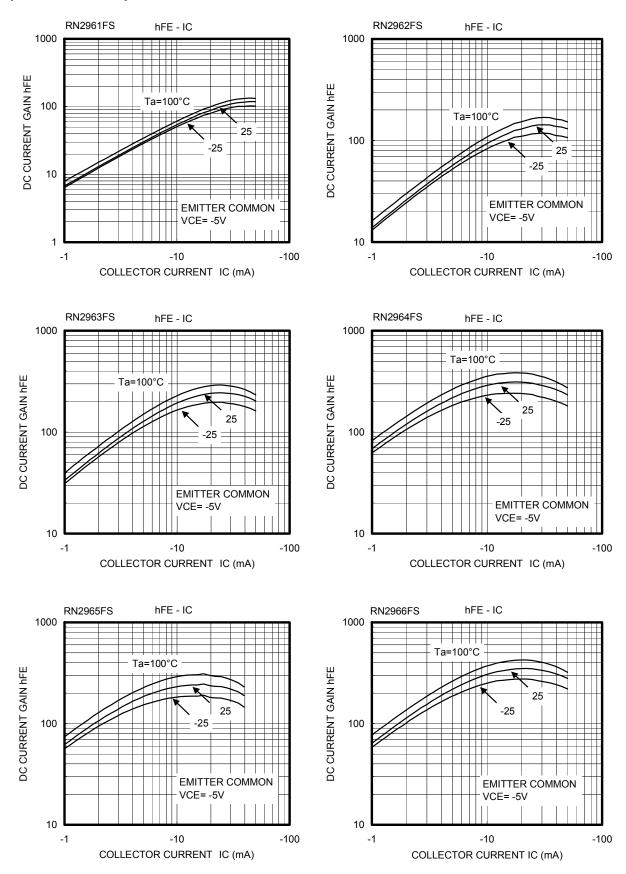


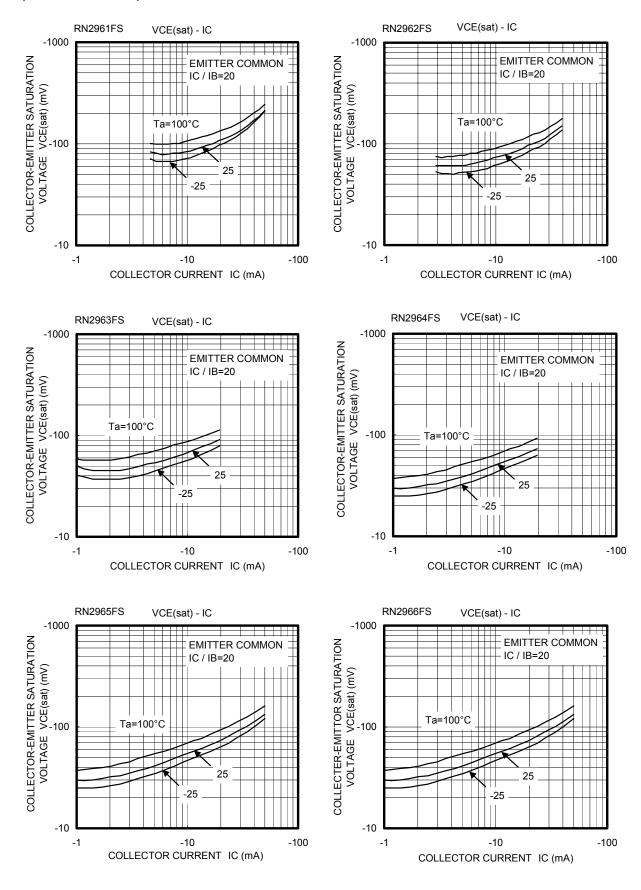


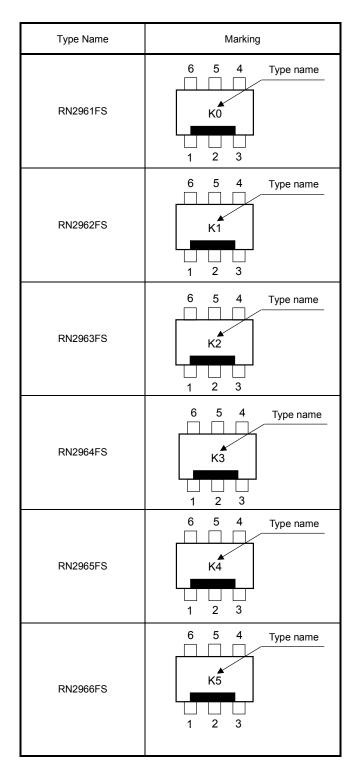












HANDLING PRECAUTION

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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